IN THE CLAIMS

Please substitute the following claims for the pending claims with the same numbers respectively:

Claim 1 (Currently amended): A nitride semiconductor laser device provided with a window layer on a light-emitting end face of a resonator which comprises an active layer of a nitride semiconductor between n-type nitride semiconductor layers and p-type nitride semiconductor layers, wherein:

at least a radiation-emitting end face of said resonator is covered by said window layer comprising monocrystalline nitride of general formula $Al_xGa_{1-x-y}In_yN$, where $0 \leq x+y \leq 1$, $0 \leq x \leq 1$ and $0 \leq y < 1$, having a wider energy gap than that of [[a]] the active layer and being formed at a low temperature so as not to damage said active layer,

wherein said window layer comprises at least one of the metals of Group I.

Claim 2 (Previously presented): The nitride semiconductor laser device according to claim 1, wherein a thickness of the end

face window layer is higher than 50 Å, and is equal to an integer multiplicity of the emitted radiation wavelength ($n\lambda$).

Claim 3 (Previously presented): The nitride semiconductor laser device according to claim 1, wherein the end face window layer is of monocrystalline $Al_xGa_{1-x}N$ ($0 \leq x \leq 1$) and is formed in a supercritical ammonia-containing solution.

Claim 4 (Previously presented): The nitride semiconductor laser device according to claim 3, wherein at least a p-type contact layer of the resonator is covered by a mask.

Claim 5 (Cancelled):

Claim 6 (Previously presented): The nitride semiconductor laser device according to claim 1, wherein the resonator active layer has a structure of a multiquantum-well layer comprising at least one InGaN well layer or InAlGaN well layer.

Claim 7 (Currently amended): The nitride semiconductor laser device according to claim 1, wherein the nitride

semiconductor laser device structure is formed on a substrate selected from the group consisting of a GaN substrate, monocrystalline GaN substrate, sapphire substrate, spinel substrate, ZnO substrate, SiC substrate, ELOG-type substrate and [[a]] the substrate provided with a nitride semiconductor having a concavo-convex face.

Claim 8 (Previously presented): The nitride semiconductor laser device according to claim 7, wherein the nitride semiconductor laser device structure is formed on a C-plane, A-plane or M-plane of the monocrystalline GaN substrate.

Claim 9 (Currently amended): [[The]] A nitride semiconductor laser device ~~according to claim 1~~, provided with a window layer on a light-emitting end face of a resonator which comprises an active layer of a nitride semiconductor between n-type nitride semiconductor layers and p-type nitride semiconductor layers, wherein:

at least a radiation-emitting end face of said resonator is covered by said window layer comprising monocrystalline nitride of general formula $Al_xGa_{1-x-y}In_yN$, where $0 \leq x+y \leq 1$, $0 \leq x \leq 1$ and $0 \leq y < 1$,

having a wider energy gap than that of the active layer and being formed at a low temperature so as not to damage said active layer, and

wherein the nitride semiconductor laser device structure is formed on a C-plane of a monocrystalline GaN substrate and the resonator end face window layer is grown on an M-plane or A-plane.

Claim 10 (Currently amended): [[The]] A nitride semiconductor laser device ~~according to claim 1~~, provided with a window layer on a light-emitting end face of a resonator which comprises an active layer of a nitride semiconductor between n-type nitride semiconductor layers and p-type nitride semiconductor layers, wherein:

at least a radiation-emitting end face of said resonator is covered by said window layer comprising monocrystalline nitride of general formula $Al_xGa_{1-x-y}In_yN$, where $0 \leq x+y \leq 1$, $0 \leq x \leq 1$ and $0 \leq y < 1$, having a wider energy gap than that of the active layer and being formed at a low temperature so as not to damage said active layer, and

wherein the nitride semiconductor laser device structure is formed on an A-plane of a monocrystalline GaN substrate, and the window layer is formed on a C-plane or M-plane of a resonator radiation-emitting end face.

Claim 11 (Currently amended): [[The]] A nitride semiconductor laser device ~~according to claim 1~~, provided with a window layer on a light-emitting end face of a resonator which comprises an active layer of a nitride semiconductor between n-type nitride semiconductor layers and p-type nitride semiconductor layers, wherein:

at least a radiation-emitting end face of said resonator is covered by said window layer comprising monocrystalline nitride of general formula $Al_xGa_{1-x-y}In_yN$, where $0 \leq x+y \leq 1$, $0 \leq x \leq 1$ and $0 \leq y < 1$, having a wider energy gap than that of the active layer and being formed at a low temperature so as not to damage said active layer, and

wherein the nitride semiconductor laser device structure is formed on an M-plane of a monocrystalline GaN substrate, and the window layer is formed on a C-plane or A-plane of a resonator radiation-emitting end face.

Claims 12-18 (Cancelled):